



PNP SURFACE MOUNT TRANSISTOR

Features

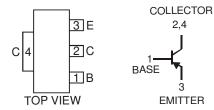
- Epitaxial Planar Die Construction
- Complementary NPN Type Available (DCX54)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

Mechanical Data

- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking & Type Code Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.072 grams (approximate)



SOT89-3L



Schematic and Pin Configuration

Maximum Ratings @TA = 25°C unless otherwise specified

| Characteristic | Symbol | Value | Unit |
|------------------------------|------------------|-------|------|
| Collector-Base Voltage | V _{CBO} | -45 | V |
| Collector-Emitter Voltage | V _{CEO} | -45 | V |
| Emitter-Base Voltage | V _{EBO} | -5 | V |
| Peak Pulse Current | I _{CM} | -1.5 | A |
| Continuous Collector Current | I _C | -1 | A |

Thermal Characteristics

| Characteristic | Symbol | Value | Unit |
|--|-------------------|-------------|------|
| Power Dissipation (Note 3) @ T _A = 25°C | P_{D} | 1 | W |
| Thermal Resistance, Junction to Ambient Air @ T _A = 25°C (Note 3) | $R_{	heta JA}$ | 125 | °C/W |
| Operating and Storage Temperature Range | T_j , T_{STG} | -55 to +150 | °C |

Electrical Characteristics @TA = 25°C unless otherwise specified

| Charac | teristic | Symbol | Min | Тур | Max | Unit | Test Conditions |
|---|-------------------------|----------------------|-----|-----|------|------|--|
| OFF CHARACTERISTICS (Note 4) | | | | | | | |
| Collector-Base Breakdown Voltage | | V _{(BR)CBO} | -45 | _ | _ | V | $I_C = -100 \mu A$, $I_E = 0 A$ |
| | | $V_{(BR)CEO}$ | -45 | _ | _ | V | $I_C = -10 \text{mA}, I_B = 0 \text{A}$ |
| Emitter-Base Breakdown Voltage | | V _{(BR)EBO} | -5 | _ | _ | V | $I_E = -10\mu A, I_C = 0A$ |
| Collector Cut-off Current | | I _{CBO} | | _ | -100 | nA | $V_{CB} = -30V, I_{E} = 0$ |
| | | | | _ | -20 | μΑ | $V_{CB} = -30V, I_{E} = 0, T_{A} = 150^{\circ}C$ |
| Emitter Cut-off Current | Emitter Cut-off Current | | | | -100 | nA | $V_{EB} = -5V, I_{C} = 0A$ |
| Emitter Cut-off Current I _{EBO} — -100 nA V _{EB} = -5V, I _C = 0A ON CHARACTERISTICS (Note 4) | | | | | | | |
| Collector-Emitter Saturation Voltage | | V _{CE(SAT)} | | | -0.5 | V | $I_C = -500 \text{mA}, I_B = -50 \text{mA}$ |
| Base-Emitter Turn-On Voltage | | V _{BE(ON)} | | | -1.0 | V | $I_C = -500 \text{mA}, V_{CE} = -2V$ |
| DC Current Gain | DCX51, DCX51-16 | h _{FE} | 63 | _ | _ | _ | $I_C = -5mA$, $V_{CE} = -2V$ |
| | | | 40 | _ | _ | _ | $I_C = -500 \text{mA}, V_{CE} = -2V$ |
| | DCX51 | | 63 | _ | 250 | _ | $I_C = -150 \text{mA}, V_{CE} = -2 \text{V}$ |
| | DCX51-16 | | 100 | | 250 | _ | $I_C = -150 \text{mA}, V_{CE} = -2 \text{V}$ |
| SMALL SIGNAL CHARACTERISTICS | | | | | | | |
| Current Gain-Bandwidth Product | | f⊤ | ١ | 200 | | MHz | $I_{C} = -50 \text{mA}, V_{CE} = -5 \text{V},$ f = 100MHz |
| Output Capacitance | | C _{obo} | | | 25 | pF | V _{CB} = -10V, f = 1MHz |

Notes: No purposefully added lead.

- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead free/index.php.
- Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- Measured under pulsed conditions. Pulse width = $300\mu s$. Duty cycle $\leq 2\%$.



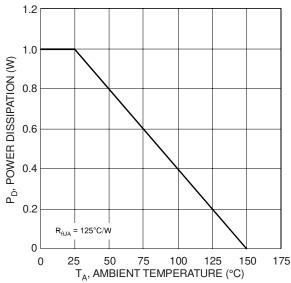


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)

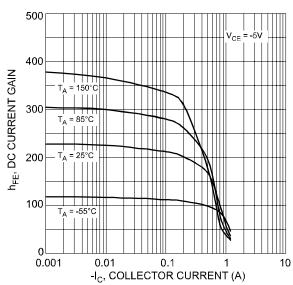


Fig. 3 Typical DC Current Gain vs. Collector Current

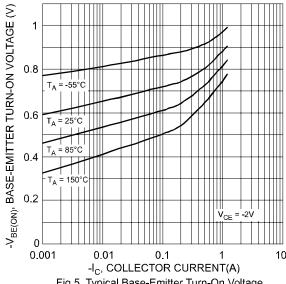
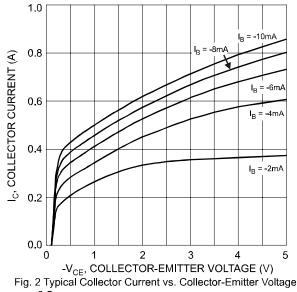


Fig 5. Typical Base-Emitter Turn-On Voltage vs. Collector Current



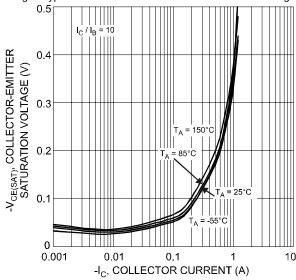


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

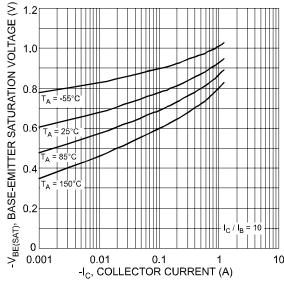
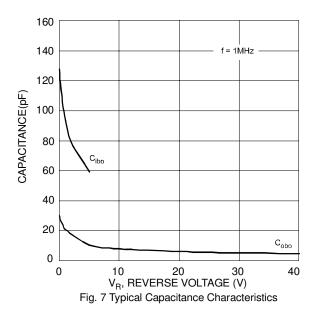


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current





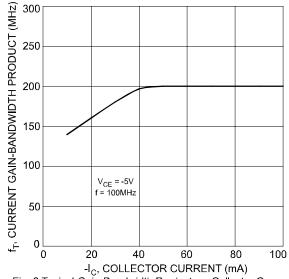


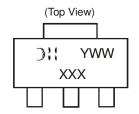
Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

Ordering Information (Note 5)

| Device | Packaging | Shipping |
|-------------|-----------|------------------|
| DCX51-13 | SOT89-3L | 2500/Tape & Reel |
| DCX51-16-13 | SOT89-3L | 2500/Tape & Reel |

5. For packaging details, go to our website at http://www.diodes.com/ap02007.pdf.

Marking Information

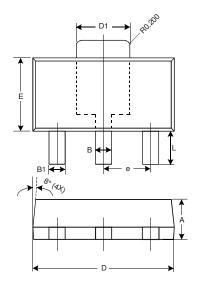


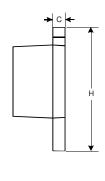
⊃!! = Manufacturer's code marking

XXX = Product type marking code Ex: P14 = DCX51 P14-16 = DCX51 -16

YWW = Date code marking Y = Last digit of year ex: 7 = 2007 WW = Week code 01 - 52

Package Outline Dimensions

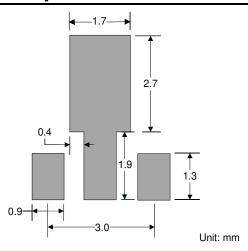




| SOT89-3L | | | | | |
|----------------------|------|------|------|--|--|
| Dim | Min | Max | Тур | | |
| Α | 1.40 | 1.60 | 1.50 | | |
| В | 0.45 | 0.55 | 0.50 | | |
| B1 | 0.37 | 0.47 | 0.42 | | |
| С | 0.35 | 0.43 | 0.38 | | |
| D | 4.40 | 4.60 | 4.50 | | |
| D1 | 1.50 | 1.70 | 1.60 | | |
| Е | 2.40 | 2.60 | 2.50 | | |
| е | _ | _ | 1.50 | | |
| Н | 3.95 | 4.25 | 4.10 | | |
| L | 0.90 | 1.20 | 1.05 | | |
| All Dimensions in mm | | | | | |



Suggested Pad Layout



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